

Bipolar Transistor

(-)160 V, (-)1.5 A, Low $V_{CE(sat)}$,
(PNP) NPN Single PCP

2SA1419, 2SC3649

Features

- Adoption of FBET, MBIT Processes
- High Breakdown Voltage and Large Current Capacity
- Ultrasmall Size Making it Easy to Provide High-density, Small-sized Hybrid IC's

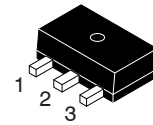
Specifications

(): 2SA1419

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CBO}	Collector-to-Base Voltage	–	(-)180	V
V_{CEO}	Collector-to-Emitter Voltage	–	(-)160	V
V_{EBO}	Emitter-to-Base Voltage	–	(-)6	V
I_C	Collector Current	–	(-)1.5	A
I_{CP}	Collector Current (Pulse)	–	(-)2.5	A
P_C	Collector Dissipation	–	500	mW
		When mounted on ceramic substrate (250 mm ² x 0.8 mm)	1.5	W
T_j	Junction Temperature	–	150	°C
T_{stg}	Storage Temperature	–	-55 to +150	°C

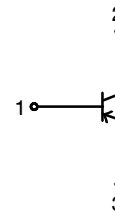
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



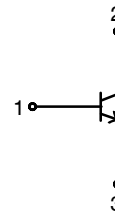
1. Base
2. Collector
3. Emitter

SOT-89 / PCP-1
CASE 419AU

ELECTRICAL CONNECTIONS

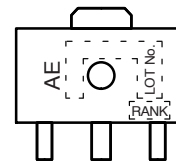


2SA1419

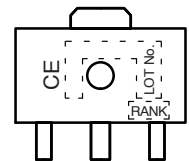


2SC3649

MARKING DIAGRAMS



2SA1419



2SC3649

AE/CE = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

2SA1419, 2SC3649

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Symbol	Parameter	Conditions	Ratings			Unit
			Min	Typ	Max	
I _{CBO}	Collector Cutoff Current	V _{CB} = (-)120 V, I _E = 0 A	-	-	(-)1	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = (-)4 V, I _C = 0 A	-	-	(-)1	μA
h _{FE1}	DC Current Gain	V _{CE} = (-)5 V, I _C = (-)100 mA	100*	-	400*	
h _{FE2}		V _{CE} = (-)5 V, I _C = (-)10 mA	80	-	-	
f _T	Gain-Bandwidth Product	V _{CE} = (-)10 V, I _C = (-)50 mA	-	120	-	MHz
C _{ob}	Output Capacitance	V _{CB} = (-)10 V, f = 1 MHz	-	(22)14	-	pF
V _{CE(sat)}	Collector-to-Emitter Saturation Voltage	I _C = (-)500 mA, I _B = (-)50 mA	-	(-200) 130	(-500) 450	mV
V _{BE(sat)}	Base-to-Emitter Saturation Voltage	I _C = (-)500 mA, I _B = (-)50 mA	-	(-)0.85	(-)1.2	V
V _{(BR)CBO}	Collector-to-Base Breakdown Voltage	I _C = (-)10 μA, I _E = 0 A	(-)180	-	-	V
V _{(BR)CEO}	Collector-to-Emitter Breakdown Voltage	I _C = (-)1 mA, R _{BE} = ∞	(-)160	-	-	V
V _{(BR)EBO}	Emitter-to-Base Breakdown Voltage	I _E = (-)10 μA, I _C = 0 A	(-)6	-	-	V
t _{on}	Turn-ON Time	See specified Test Circuit	-	(40) 40	-	ns
t _{stg}	Storage Time		-	(0.7) 1.2	-	μs
t _f	Fall Time		-	(40) 80	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

* The 2SA1419 / 2SC3649 are classified by 100 mA h_{FE} as follows:

Rank	R	S	T
h _{FE}	100 to 200	140 to 280	200 to 400

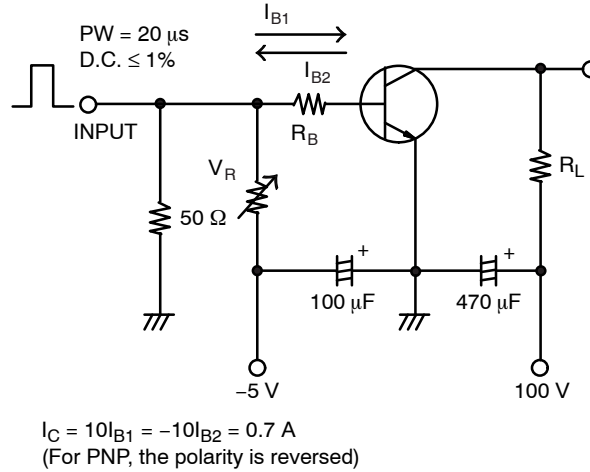


Figure 1. Switching Time Test Circuit

TYPICAL CHARACTERISTICS

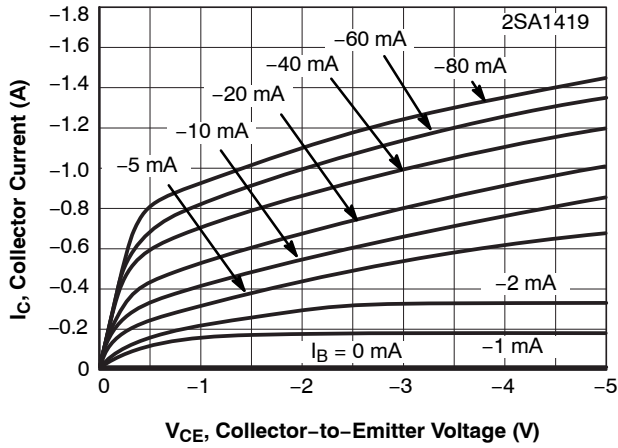


Figure 2. $I_C - V_{CE}$

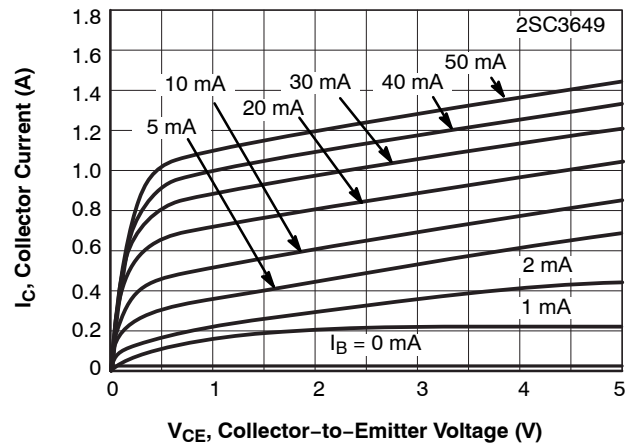


Figure 3. $I_C - V_{CE}$

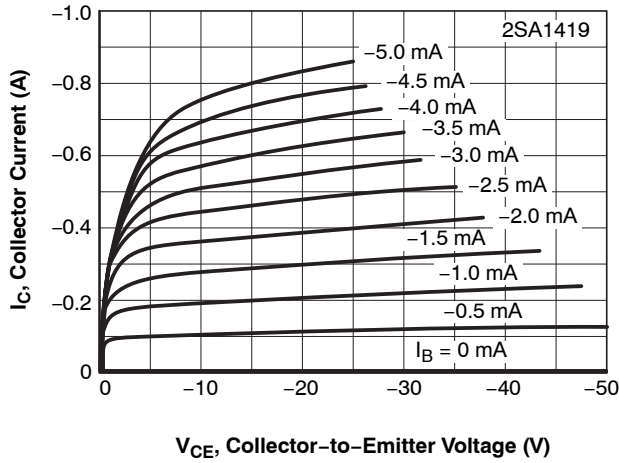


Figure 4. $I_C - V_{CE}$

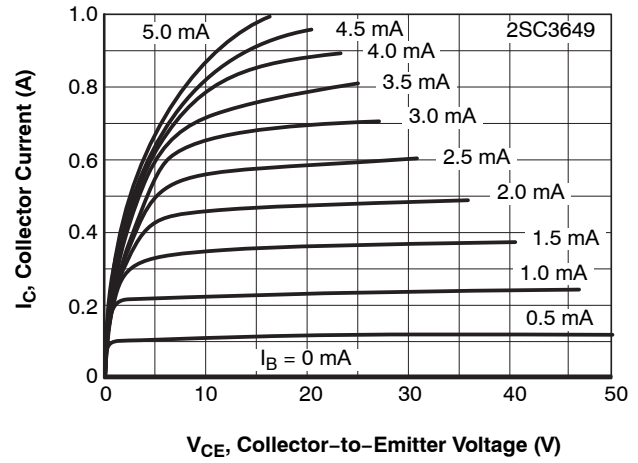


Figure 5. $I_C - V_{CE}$

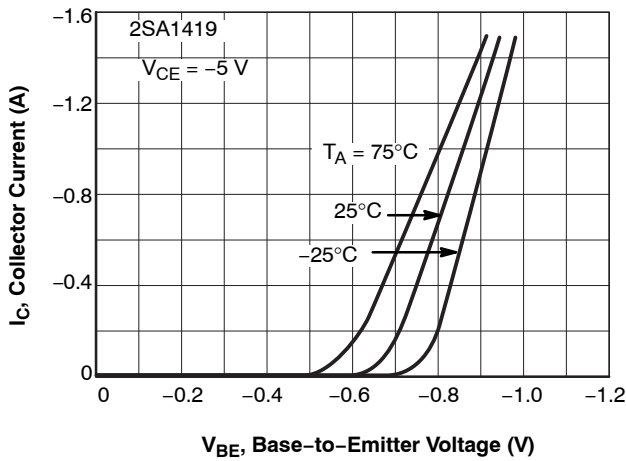


Figure 6. $I_C - V_{BE}$

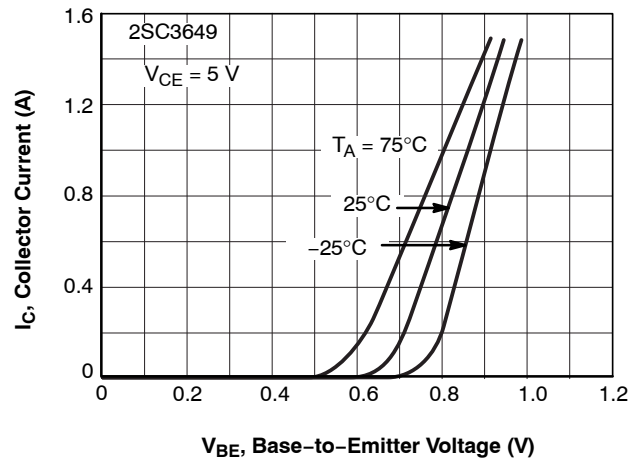


Figure 7. $I_C - V_{BE}$

TYPICAL CHARACTERISTICS (continued)

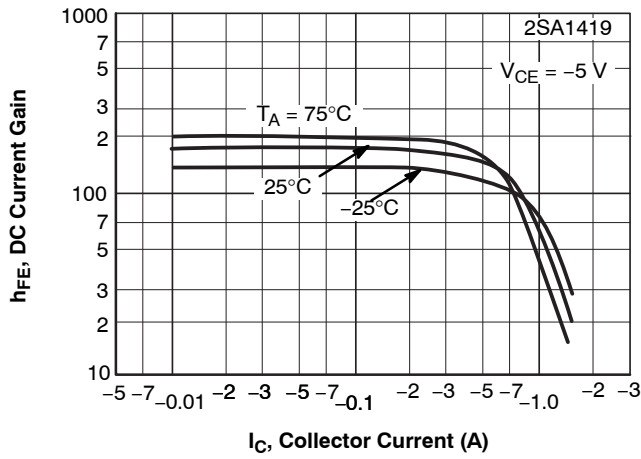


Figure 8. $h_{FE} - I_C$

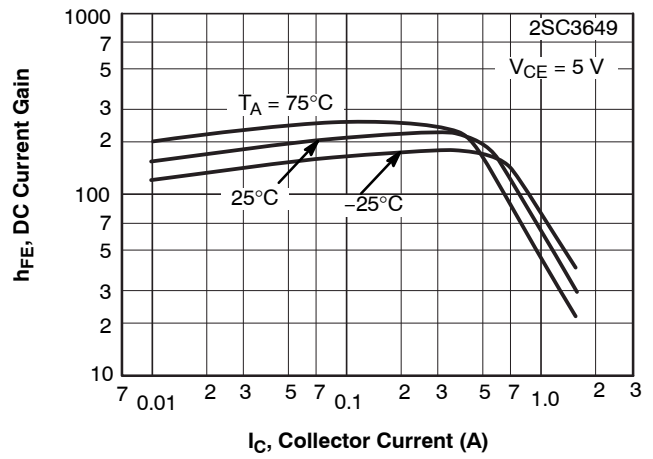


Figure 9. $h_{FE} - I_C$

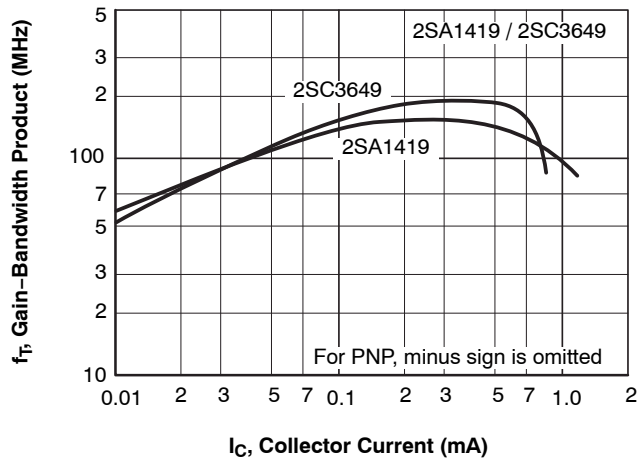


Figure 10. $f_T - I_C$

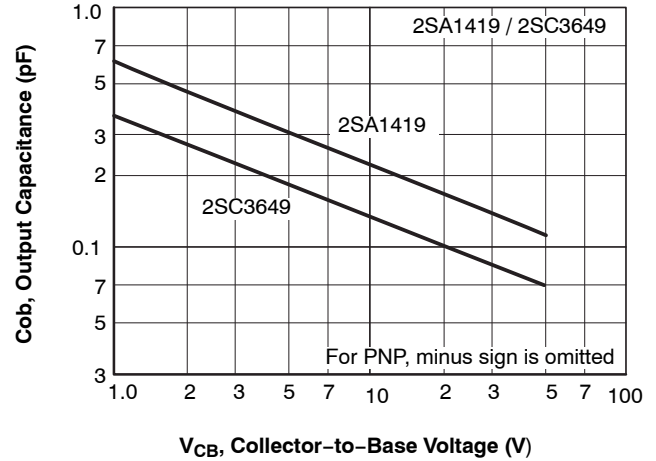


Figure 11. $C_{ob} - V_{CB}$

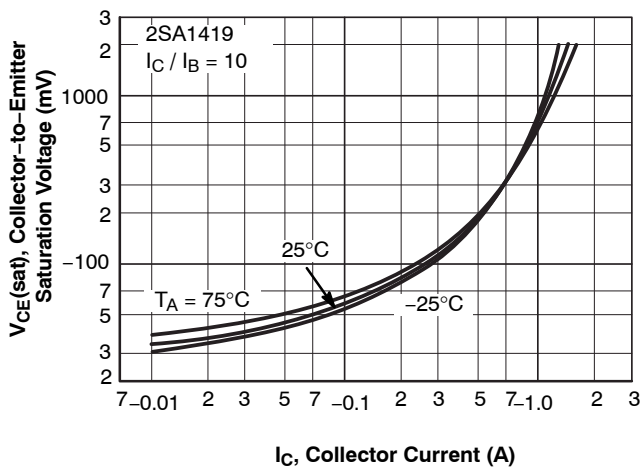


Figure 12. $V_{CE(sat)} - I_C$

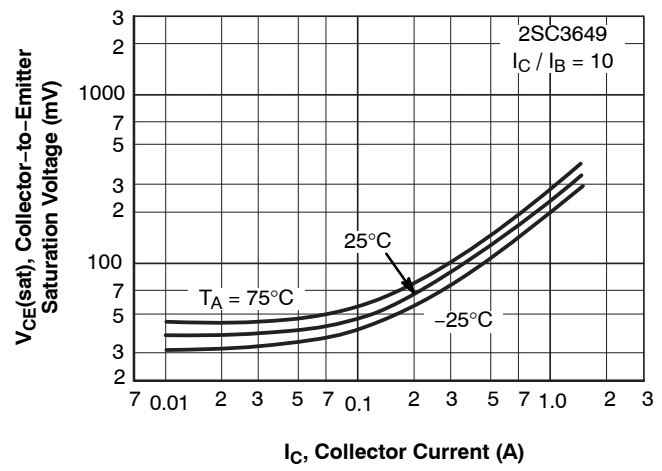


Figure 13. $V_{CE(sat)} - I_C$

2SA1419, 2SC3649

TYPICAL CHARACTERISTICS (continued)

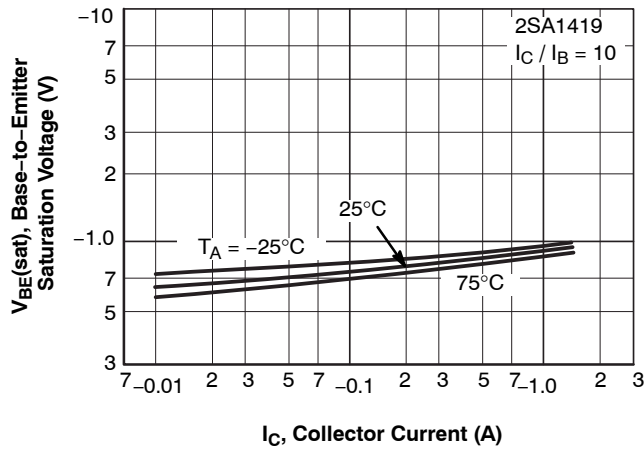


Figure 14. $V_{BE}(sat) - I_C$

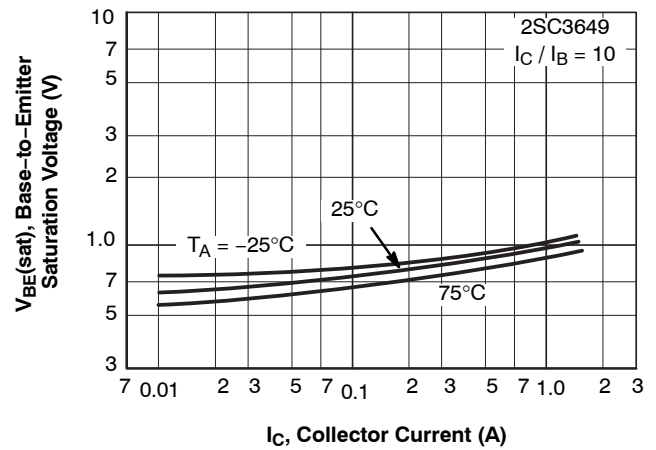


Figure 15. $V_{BE}(sat) - I_C$

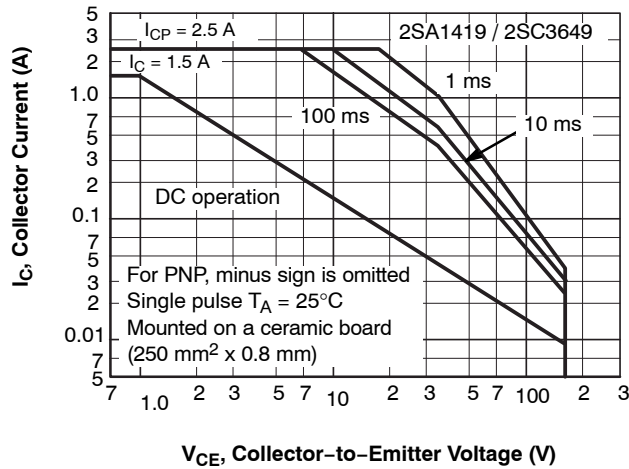


Figure 16. ASO

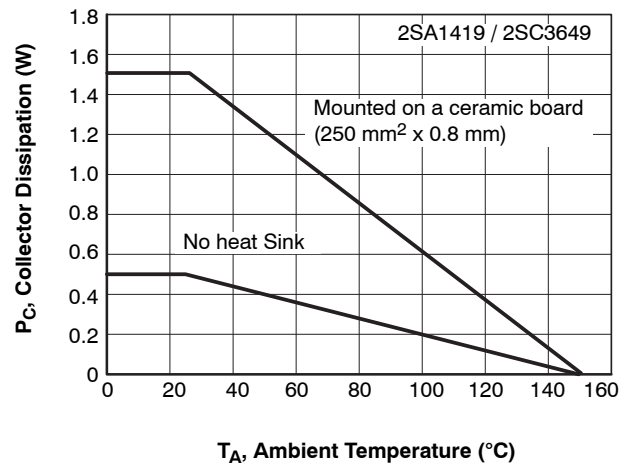
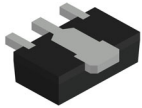


Figure 17. $P_C - T_A$

ORDERING INFORMATION

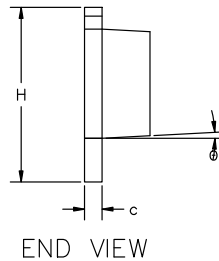
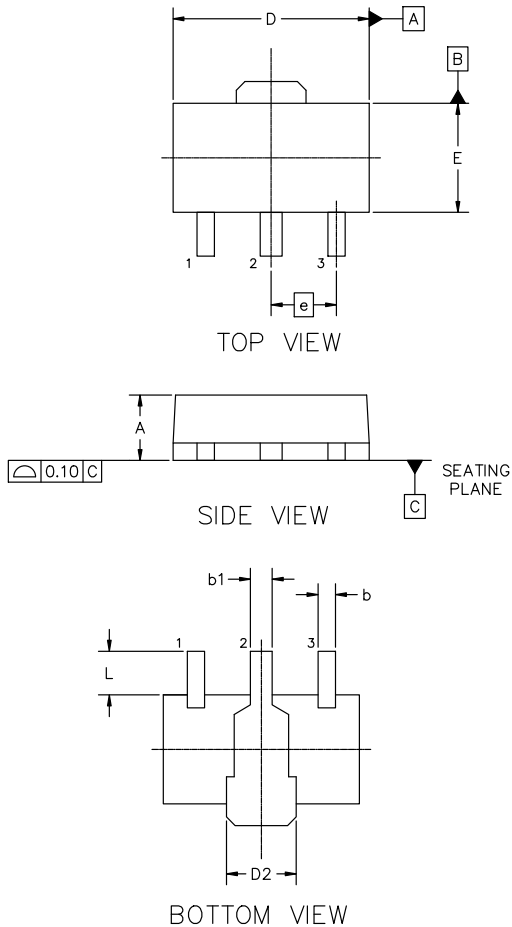
Device	Package	Shipping [†]
2SA1419S-TD-E	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel
2SA1419T-TD-E	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel
2SA1419T-TD-H	SOT-89 / PCP-1 (Pb-Free, Halide Free)	1000 / Tape & Reel
2SC3649S-TD-E	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel
2SC3649S-TD-H	SOT-89 / PCP-1 (Pb-Free & Halogen Free)	1000 / Tape & Reel
2SC3649T-TD-E	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel
2SC3649T-TD-H	SOT-89 / PCP-1 (Pb-Free & Halogen Free)	1000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).



SOT-89 4.50x2.50x1.50 1.50P
CASE 419AU
ISSUE A

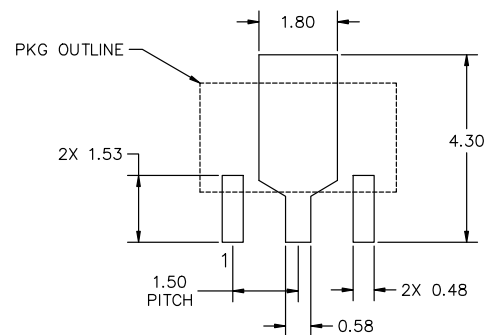
DATE 21 MAY 2025



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS INCLUDES LEAD FINISH.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.40	1.50	1.60
b	0.35	0.40	0.48
b1	0.40	0.50	0.55
c	0.37	0.40	0.43
D	4.40	4.50	4.60
D2	1.40	1.60	1.80
E	2.40	2.50	2.60
e	1.50 BSC		
H	3.80	4.00	4.20
L	0.80	1.00	1.20
θ	0°	---	3°



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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DESCRIPTION:	SOT-89 4.50x2.50x1.50 1.50P	PAGE 1 OF 1

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